

UNIT

V

Ω

nC

N-Channel Power MOSFET

700V, 8A, 0.6Ω

FEATURES

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance

APPLICATION

- Power Supply
- Lighting





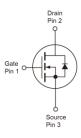
TO-252 (DPAK)

PARAMETER

 V_{DS}

R_{DS(on)} (max)

Qg



KEY PERFORMANCE PARAMETERS

VALUE

700

0.6

12.6

HALOGEN FREE

Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	ITO-220	IPAK/DPAK	UNIT
Drain-Source Voltage		V _{DS}	700		V
Gate-Source Voltage		V _{GS}	±30		V
Continuous Drain Current (Note 1)	$T_{\rm C} = 25^{\circ}{\rm C}$		8 4.8		A
	$T_{\rm C} = 100^{\circ}{\rm C}$	l _D			
Pulsed Drain Current (Note 2)		I _{DM}	24		А
Total Power Dissipation @ $T_c = 25^{\circ}C$		P _{DTOT}	32	83	W
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	100		mJ
Single Pulsed Avalanche Current (Note 3)		I _{AS}	2		А
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150		°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	ITO-220	IPAK/DPAK	UNIT
Junction to Case Thermal Resistance	R _{eJC}	3.9	1.5	°C/W
Junction to Ambient Thermal Resistance	R _{⊖JA}	62 62		°C/W

Notes: R_{0JA} is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. R_{BJA} is guaranteed by design while R_{BCA} is determined by the user's board design. R_{0JA} shown below for single device operation on FR-4 PCB in still air.



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ELECTRICAL SPECIFICATIONS ($T_A = 25^{\circ}C$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250 \mu A$	BV _{DSS}	700			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V _{GS(TH)}	2	2.9	4	V
Gate Body Leakage	$V_{GS} = \pm 30 \text{V}, V_{DS} = 0 \text{V}$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 700V, V_{GS} = 0V$	I _{DSS}			1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_{D} = 4A$	R _{DS(on)}		0.5	0.6	Ω
Dynamic ^(Note 5)						
Total Gate Charge	$V_{\rm DS} = 380V, I_{\rm D} = 8A,$	Qg		12.6		
Gate-Source Charge		Q _{gs}		2.9		nC
Gate-Drain Charge	V _{GS} = 10V	Q _{gd}		4.5		
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C _{iss}		743		
Output Capacitance	f = 1.0MHz	C _{oss}		63		pF
Gate Resistance	F = 1MHz, open drain	R _g		3.19		Ω
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = 380V,$ $R_{GEN} = 25\Omega,$ $I_{D} = 8A, V_{GS} = 10V,$	t _{d(on)}		21		
Turn-On Rise Time		t _r		15		
Turn-Off Delay Time		t _{d(off)}		40		ns
Turn-Off Fall Time	ID = OA, VGS = 10V,	t _f		9		
Source-Drain Diode (Note 4)						
Forward On Voltage	$I_{\rm S} = 8$ A, $V_{\rm GS} = 0$ V	V _{SD}		0.84	1.4	V
Reverse Recovery Time	V _R =200V, I _S = 4A	t _{rr}		187.9		ns
Reverse Recovery Charge	dl _F /dt = 100A/µs	Q _{rr}		1.4		μC

Notes:

1. Current limited by package

2. Pulse width limited by the maximum junction temperature

3. L = 50mH, I_{AS} = 2A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}$ C

4. Pulse test: PW \leq 300µs, duty cycle \leq 2%

5. For DESIGN AID ONLY, not subject to production testing.

6. Switching time is essentially independent of operating temperature.



ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM70N600CI C0G	ITO-220	50pcs / Tube
TSM70N600CH C5G	TO-251 (IPAK)	75pcs / Tube
TSM70N600CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

Note:

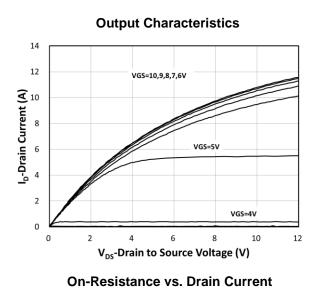
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

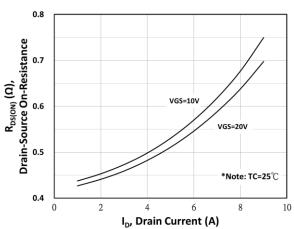
2. Halogen-free according to IEC 61249-2-21 definition



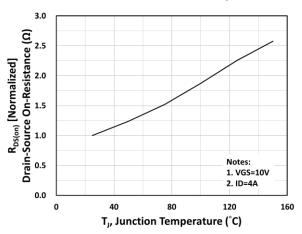
CHARACTERISTICS CURVES

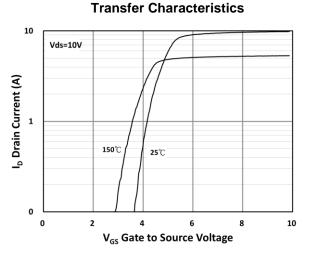
 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$



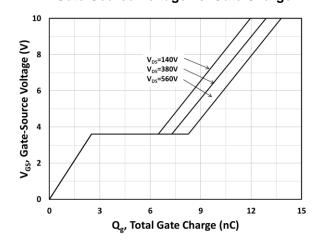


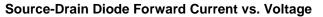
On-Resistance vs. Junction Temperature

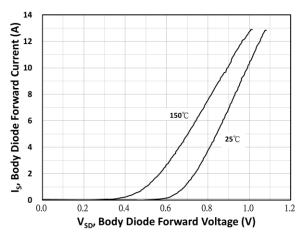




Gate-Source Voltage vs. Gate Charge



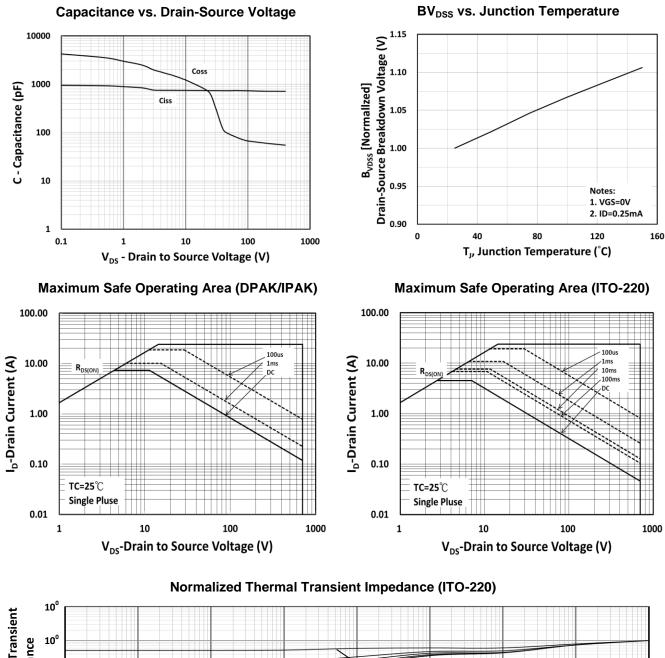


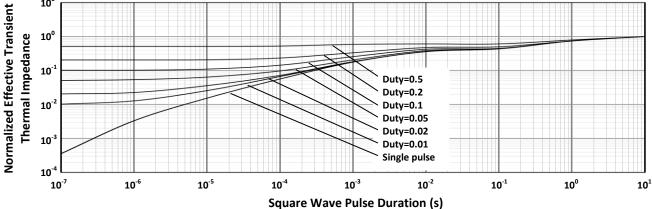




CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

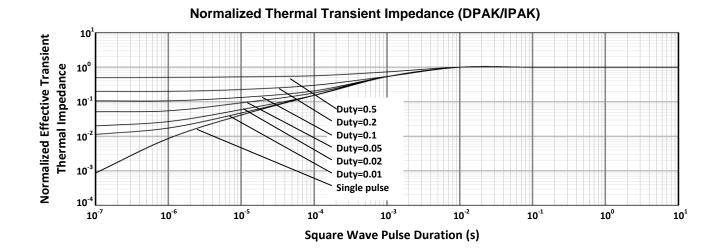




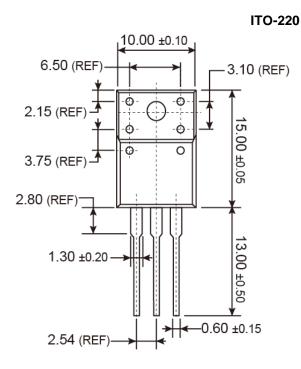


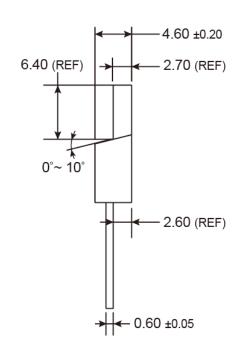
ELECTRICAL CHARACTERISTICS CURVES

 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$





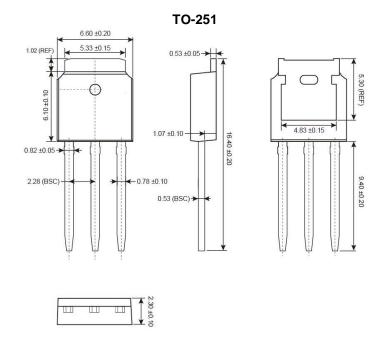






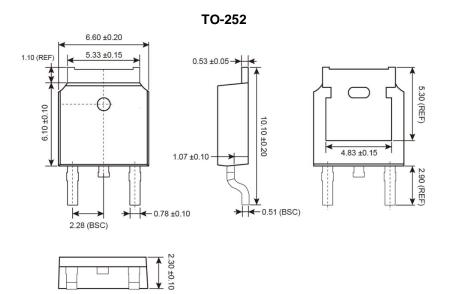
- G = Halogen FreeY = Year Code
- WW = Week Code (01~52)
 - **F** = Factory Code



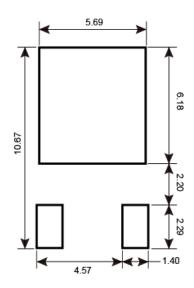


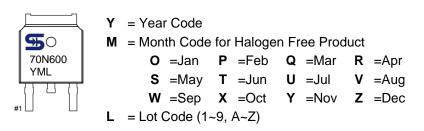
50	Y = Year CodeM = Month Code for Halogen Free Product
70N600 YML	O =Jan P =Feb Q =Mar R =Apr
	S =May T =Jun U =Jul V =Aug
	W =Sep X =Oct Y =Nov Z =Dec
#1	L = Lot Code (1~9, A~Z)



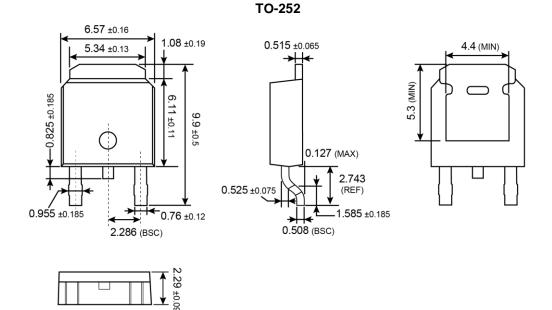


SUGGESTED PAD LAYOUT (Unit: Millimeters)

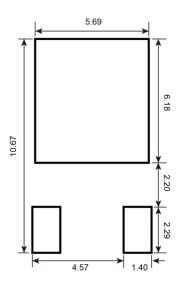


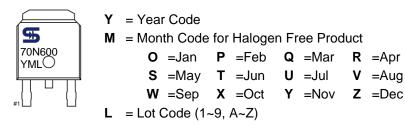






SUGGESTED PAD LAYOUT (Unit: Millimeters)







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